



# IMPORTANT NOTICE

10 December 2015

## 1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

**WWW** - For [www.nxp.com](http://www.nxp.com) use [www.ween-semi.com](http://www.ween-semi.com)

**Email** - For [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com) use [salesaddresses@ween-semi.com](mailto:salesaddresses@ween-semi.com)

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If you have any questions related to this document, please contact our nearest sales office via e-mail or phone (details via [salesaddresses@ween-semi.com](mailto:salesaddresses@ween-semi.com)).

Thank you for your cooperation and understanding,

WeEn Semiconductors



## Silicon Diffused Power Transistor

PHE13009

## GENERAL DESCRIPTION

The PHE13009 is a silicon npn power switching transistor in the TO220AB envelope intended for use in high frequency electronic lighting ballast applications, converters, inverters, switching regulators, motor control systems, etc.

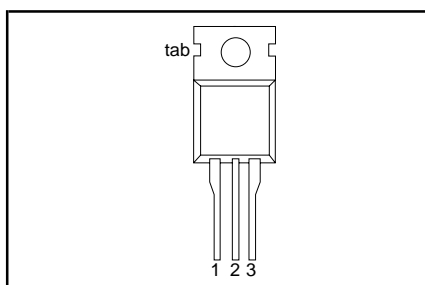
## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$V_{CESM}$	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	700	V
$V_{CBO}$	Collector-Base voltage (open emitter)		-	700	V
$V_{CEO}$	Collector-emitter voltage (open base)		-	400	V
$I_C$	Collector current (DC)		-	12	A
$I_{CM}$	Collector current peak value		-	24	A
$P_{tot}$	Total power dissipation	$T_{mb} \leq 25\text{ }^\circ\text{C}$	-	80	W
$V_{CESat}$	Collector-emitter saturation voltage	$I_C = 5.0\text{ A}; I_B = 1.0\text{ A}$	0.32	1.0	V
$h_{FEsat}$		$I_C = 5.0\text{ A}; V_{CE} = 5\text{ V}$	-	40	
$t_f$	Fall time	$I_C = 5.0\text{ A}; I_{B1} = 1.0\text{ A}$	0.1	0.5	$\mu\text{s}$

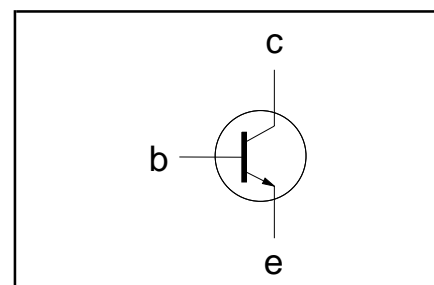
## PINNING - TO220AB

PIN	DESCRIPTION
1	base
2	collector
3	emitter
tab	collector

## PIN CONFIGURATION



## SYMBOL



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CESM}$	Collector to emitter voltage	$V_{BE} = 0\text{ V}$	-	700	V
$V_{CEO}$	Collector to emitter voltage (open base)		-	400	V
$V_{CBO}$	Collector to base voltage (open emitter)		-	700	V
$I_C$	Collector current (DC)		-	12	A
$I_{CM}$	Collector current peak value		-	24	A
$I_B$	Base current (DC)		-	6	A
$I_{BM}$	Base current peak value		-	12	A
$P_{tot}$	Total power dissipation	$T_{mb} \leq 25\text{ }^\circ\text{C}$	-	80	W
$T_{stg}$	Storage temperature		-65	150	$^\circ\text{C}$
$T_j$	Junction temperature		-	150	$^\circ\text{C}$

## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Junction to mounting base		-	1.56	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	60	-	K/W

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**STATIC CHARACTERISTICS** $T_{mb} = 25\text{ °C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CES}, I_{CBO}$ $I_{CES}$	Collector cut-off current <sup>1</sup>	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_j = 125\text{ °C}$	-	-	1.0 5.0	mA mA
$I_{CEO}$ $I_{EBO}$ $V_{CEOsust}$	Collector cut-off current Emitter cut-off current Collector-emitter sustaining voltage	$V_{CEO} = V_{CEOMmax} (400V)$ $V_{EB} = 9\text{ V}; I_C = 0\text{ A}$ $I_B = 0\text{ A}; I_C = 10\text{ mA};$ $L = 25\text{ mH}$	-	-	0.1 1 -	mA mA V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C = 5.0\text{ A}; I_B = 1.0\text{ A}$ $I_C = 8.0\text{ A}; I_B = 1.6\text{ A}$	-	0.32 -	1.0 2.0	V V
$V_{BEsat}$	Base-emitter saturation voltage	$I_C = 5.0\text{ A}; I_B = 1.0\text{ A}$ $I_C = 8.0\text{ A}; I_B = 1.6\text{ A}$	-	1.0 1.1	1.3 1.6	V V
$h_{FE}$ $h_{FEsat}$	DC current gain	$I_C = 5.0\text{ A}; V_{CE} = 5\text{ V}$ $I_C = 8.0\text{ A}; V_{CE} = 5\text{ V}$	8 6	- -	40 30	

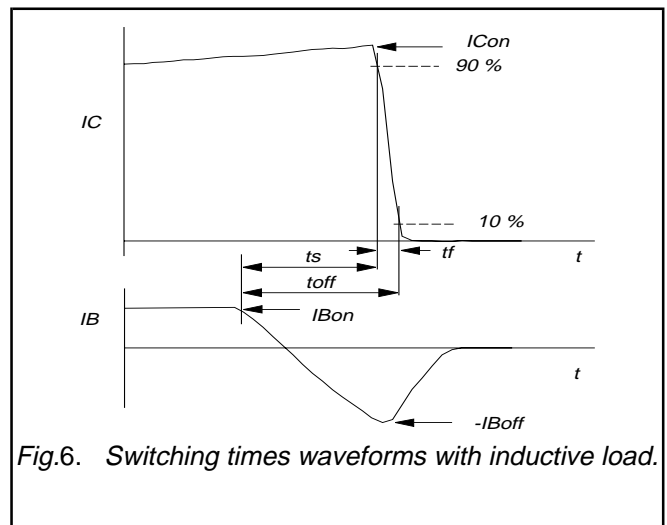
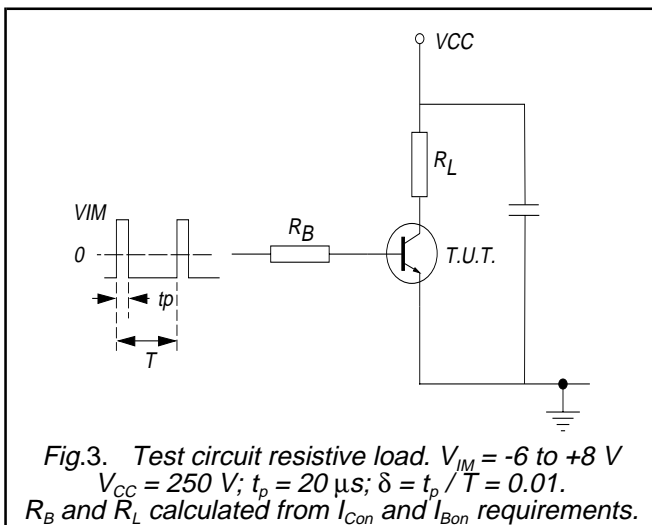
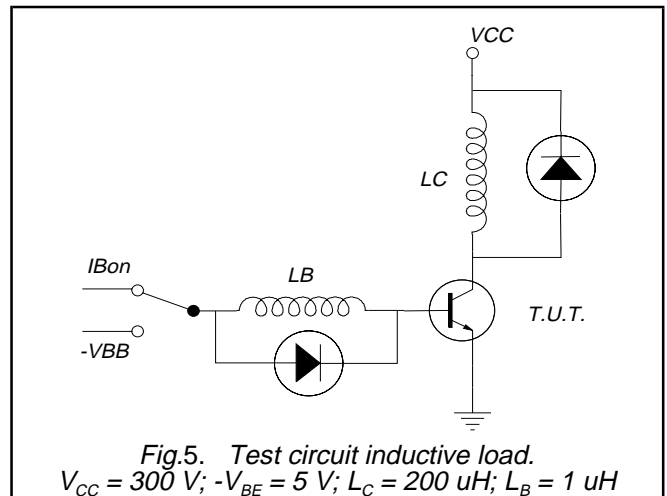
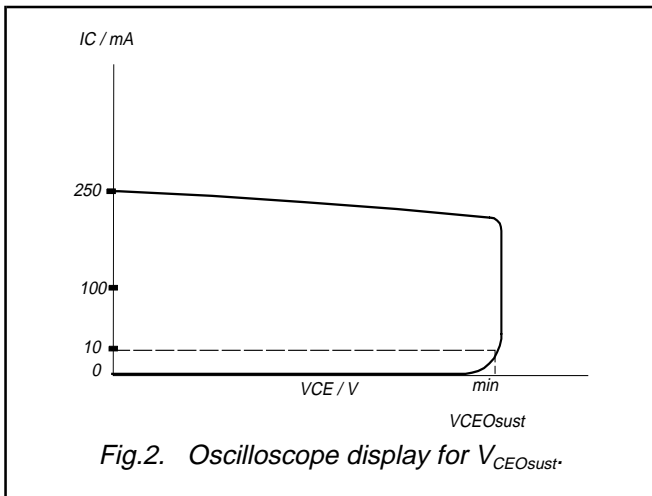
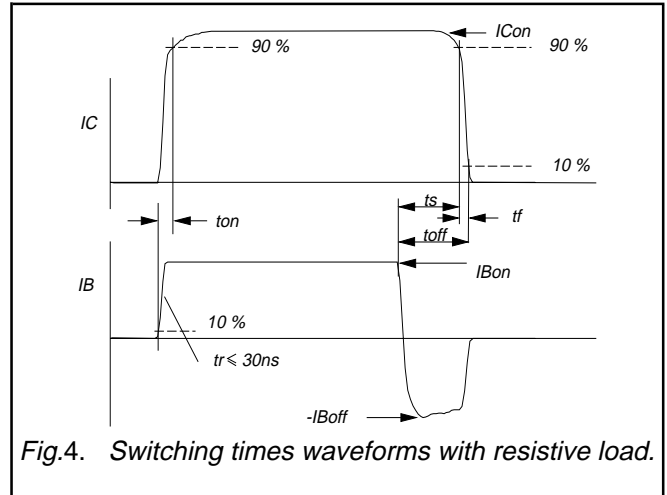
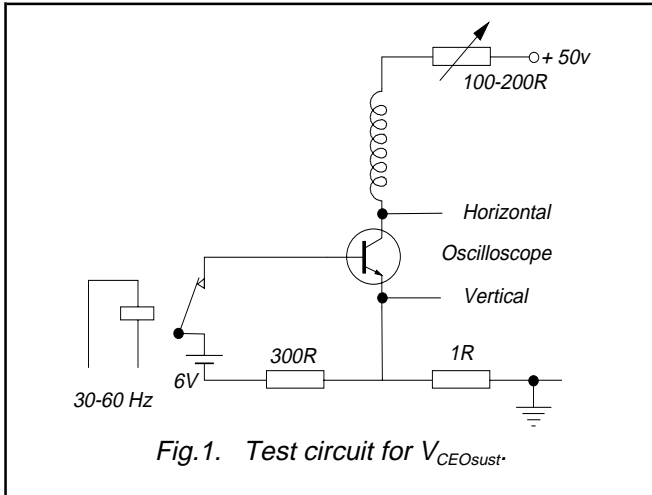
**DYNAMIC CHARACTERISTICS** $T_{mb} = 25\text{ °C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$t_s$ $t_f$	Switching times (resistive load) Turn-off storage time Turn-off fall time	$I_{Con} = 5\text{ A}; I_{Bon} = -I_{Boff} = 1\text{ A};$ $R_L = 75\text{ ohms}; V_{BB2} = 4\text{ V};$	2.2 0.26	3.3 0.7	$\mu\text{s}$ $\mu\text{s}$
$t_s$ $t_f$	Switching times (inductive load) Turn-off storage time Turn-off fall time	$I_{Con} = 5\text{ A}; I_{Bon} = 1\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}$	1.35 0.1	2.3 0.5	$\mu\text{s}$ $\mu\text{s}$
$t_s$ $t_f$	Switching times (inductive load) Turn-off storage time Turn-off fall time	$I_{Con} = 5\text{ A}; I_{Bon} = 1\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}; T_j = 100\text{ °C}$	- -	3.2 0.9	$\mu\text{s}$ $\mu\text{s}$

<sup>1</sup> Measured with half sine-wave voltage (curve tracer).

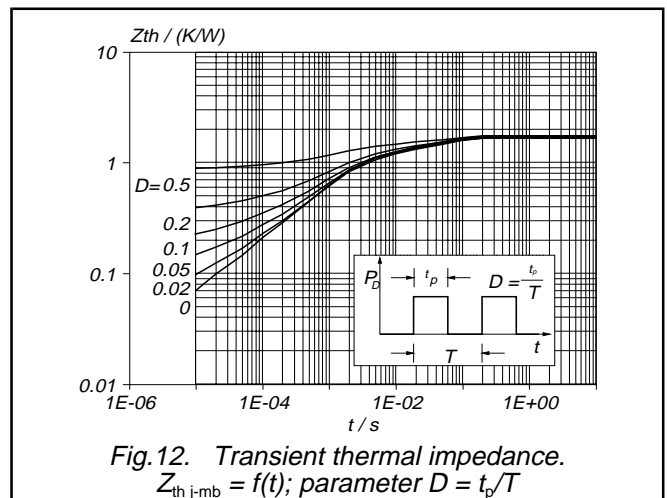
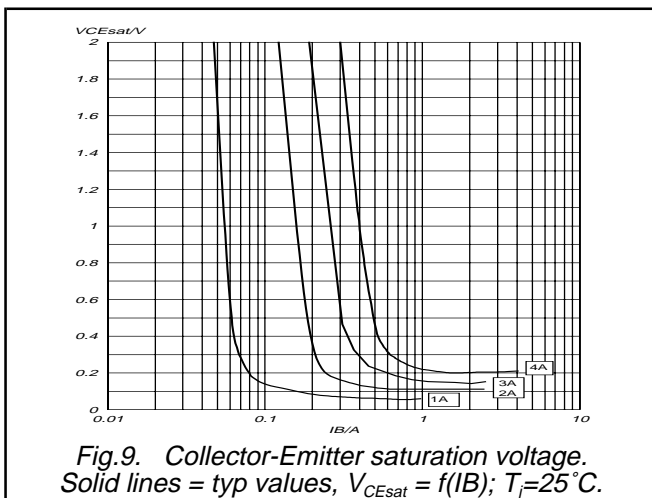
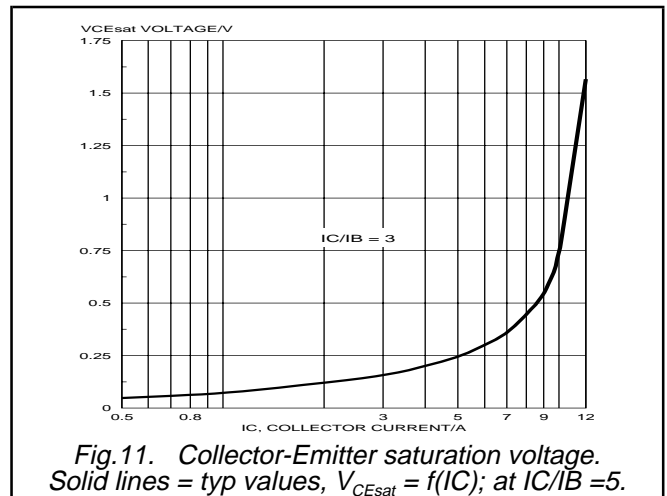
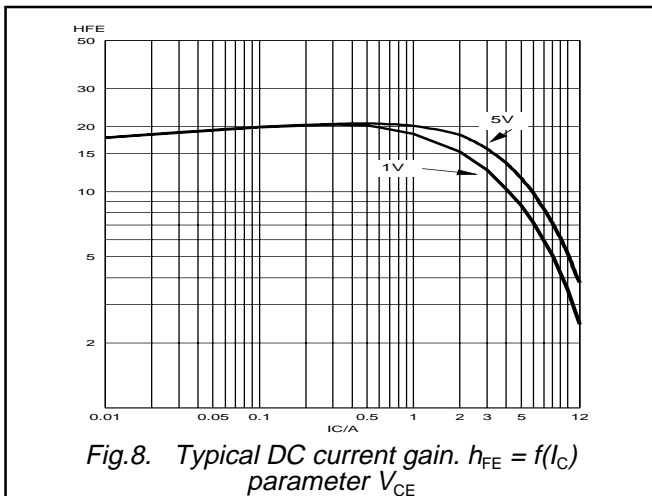
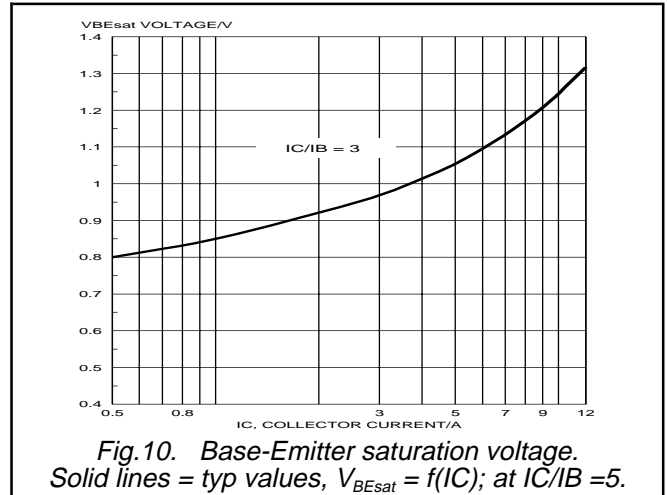
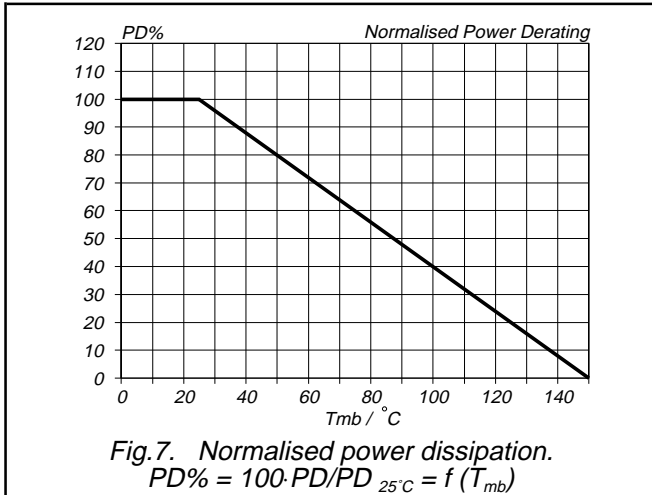
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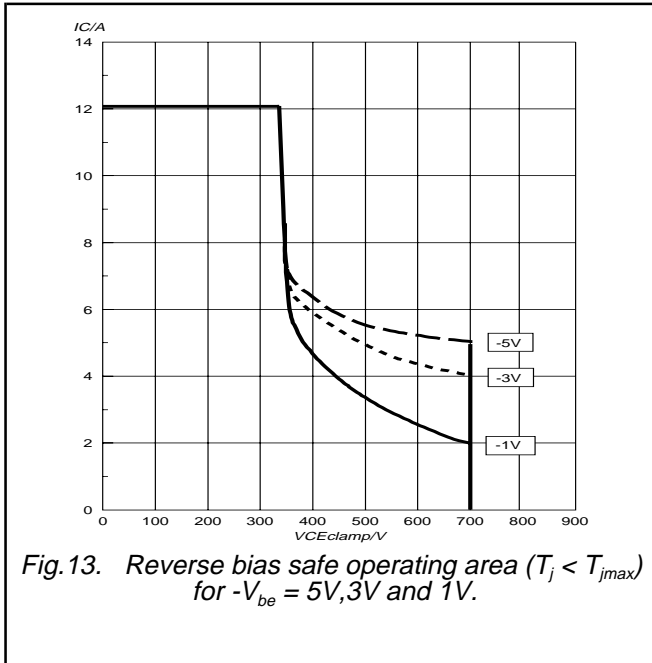


Fig.13. Reverse bias safe operating area ( $T_j < T_{jmax}$ ) for  $-V_{be} = 5V, 3V$  and  $1V$ .

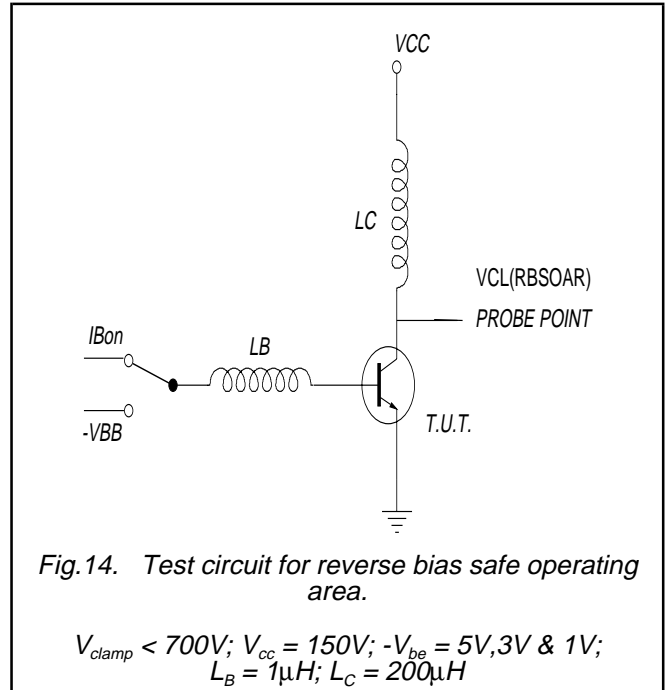


Fig.14. Test circuit for reverse bias safe operating area.

$V_{clamp} < 700V$ ;  $V_{cc} = 150V$ ;  $-V_{be} = 5V, 3V$  &  $1V$ ;  
 $L_B = 1\mu H$ ;  $L_C = 200\mu H$

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**MECHANICAL DATA**

*Dimensions in mm*

*Net Mass: 2 g*

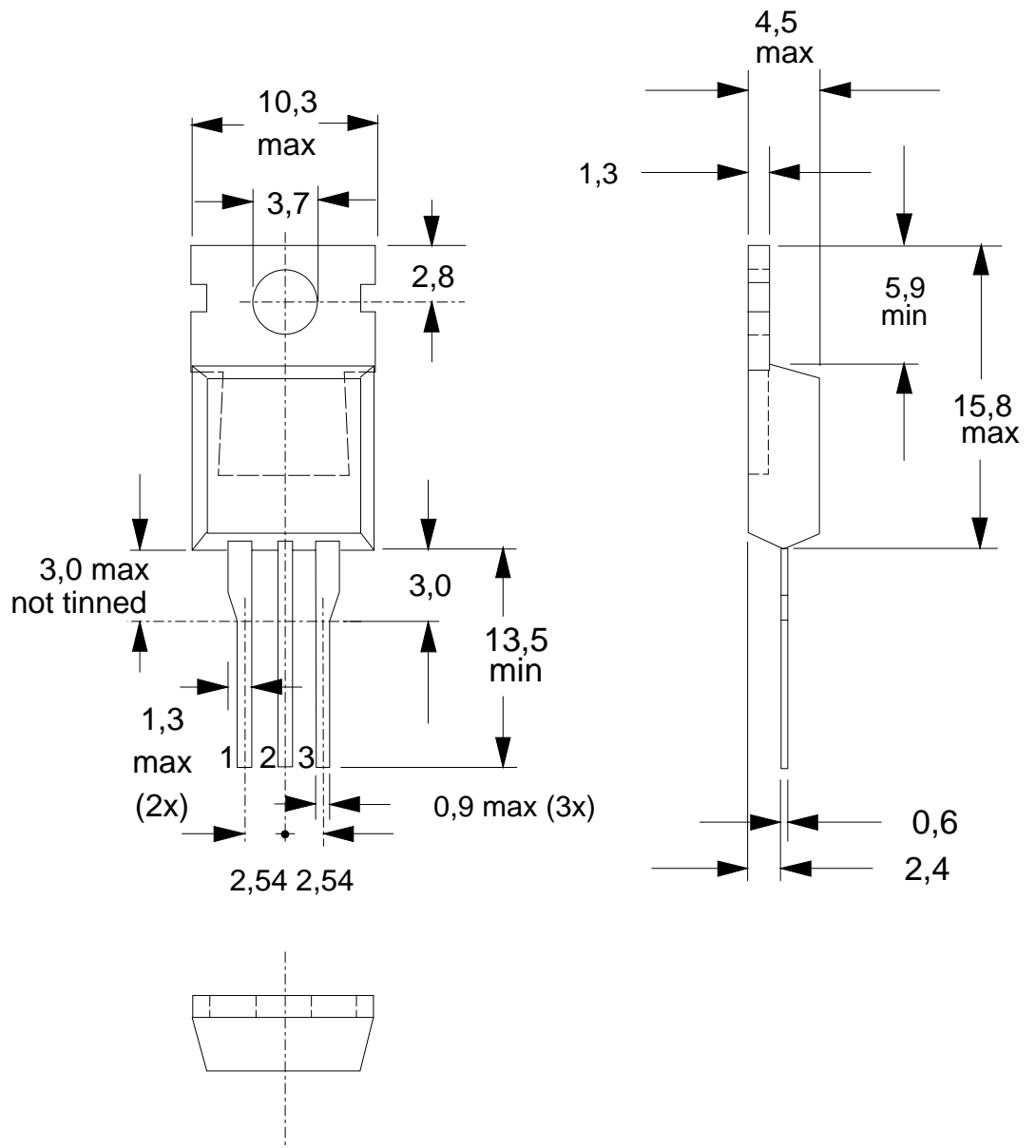


Fig.15. TO220AB; pin 2 connected to mounting base.

**Notes**

1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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**DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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